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Sunder

Docket No.: M4065.0381/P381
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Leonard Forbes, et al.

Application No.: 09/808,114

Group Art Unit: 2826

Filed: March 15, 2001

Examiner: K. Quinto

For: TECHNIQUE TO MITIGATE SHORT
CHANNEL EFFECTS WITH VERTICAL
GATE TRANSISTOR WITH DIFFERENT
GATE MATERIALS

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AMENDMENT

Box Non-Fee Amendment
Commissioner for Patents
Washington, DC 20231

Dear Sir:

In response to the Office Action dated December 4, 2002 (Paper No. 9), please
amend the above-identified U.S. patent application as follows:

In the Claims:

Please replace selected claims with the respective amended claims set forth
below.

1. (Amended) A semiconductor device comprising:

Q1
a substrate having at least two spaced doped source/drain regions, said
source/drain regions defining a channel region therebetween; and